

SN74CB3Q3253 Dual 1-of-4 FET Multiplexer – Demultiplexer **2.5-V – 3.3-V Low-Voltage High-Bandwidth Bus Switch**

1 Features

- High-Bandwidth Data Path (Up to 500 MHz) ⁽¹⁾
- 5-V Tolerant I/Os With Device Powered Up or Powered Down
- Low and Flat ON-State Resistance (r_{on}) Characteristics Over Operating Range ($r_{on} = 4\ \Omega$ Typical)
- Rail-to-Rail Switching on Data I/O Ports
 - 0- to 5-V Switching With 3.3-V V_{CC}
 - 0- to 3.3-V Switching With 2.5-V V_{CC}
- Bidirectional Data Flow With Near-Zero Propagation Delay
- Low Input/Output Capacitance Minimizes Loading and Signal Distortion ($C_{iO(OFF)} = 3.5\text{ pF}$ Typical)
- Fast Switching Frequency ($f_{OE} = 20\text{ MHz}$ Max)
- Data and Control Inputs Provide Undershoot Clamp Diodes
- Low Power Consumption ($I_{CC} = 0.6\text{ mA}$ Typical)
- V_{CC} Operating Range From 2.3 V to 3.6 V
- Data I/Os Support 0- to 5-V Signal Levels (0.8-V, 1.2-V, 1.5-V, 1.8-V, 2.5-V, 3.3-V, 5-V)
- Control Inputs Can be Driven by TTL or 5-V and 3.3-V CMOS Outputs
- I_{off} Supports Partial-Power-Down Mode Operation
- Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II
- ESD Performance Tested Per JESD 22
 - 2000-V Human-Body Model (A114-B, Class II)
 - 1000-V Charged-Device Model (C101)
- Supports Both Digital and Analog Applications: USB Interface, Differential Signal Interface Bus Isolation, Low-Distortion Signal Gating

⁽¹⁾ For additional information regarding the performance characteristics of the CB3Q family, refer to the TI application report *CBT-C, CB3T, and CB3Q Signal-Switch Families*, (SCDA008).

2 Applications

- Video Broadcasting: IP-Based Multi-Format Transcoder
- Video Communications System

3 Description

The SN74CB3Q3253 device is a high-bandwidth FET bus switch using a charge pump to elevate the gate voltage of the pass transistor, providing a low and flat ON-state resistance (r_{on}). The low and flat ON-state resistance allows for minimal propagation delay and supports rail-to-rail switching on the data input and output (I/O) ports.

Device Information

PART NUMBER	PACKAGE	BODY SIZE (NOM)
SN74CB3Q3253DBQ	SSOP (16)	4.90 mm × 3.90 mm
SN74CB3Q3253DGV	TVSOP (16)	3.60 mm × 4.40 mm
SN74CB3Q3253RGY	VQFN (16)	4.00 mm × 3.50 mm
SN74CB3Q3253PW	TSSOP (16)	5.00 mm × 4.40 mm

⁽¹⁾ For all available packages, see the orderable addendum at the end of the data sheet.

Logic Diagram (Positive Logic)

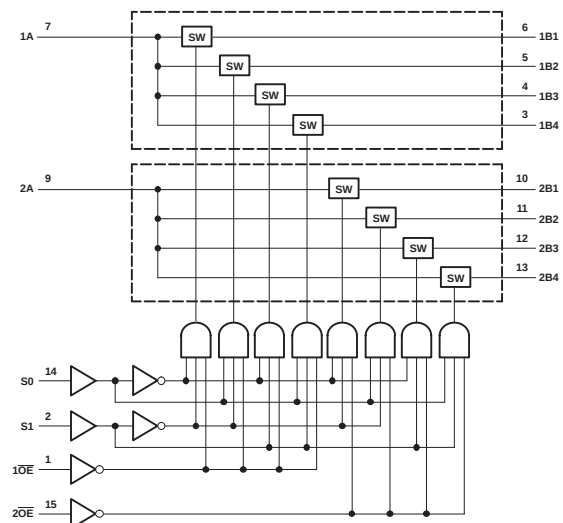


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4 Revision History

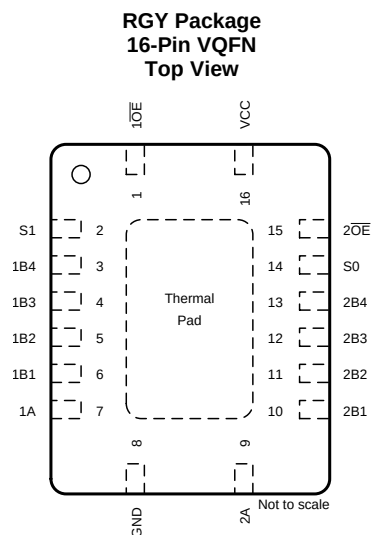
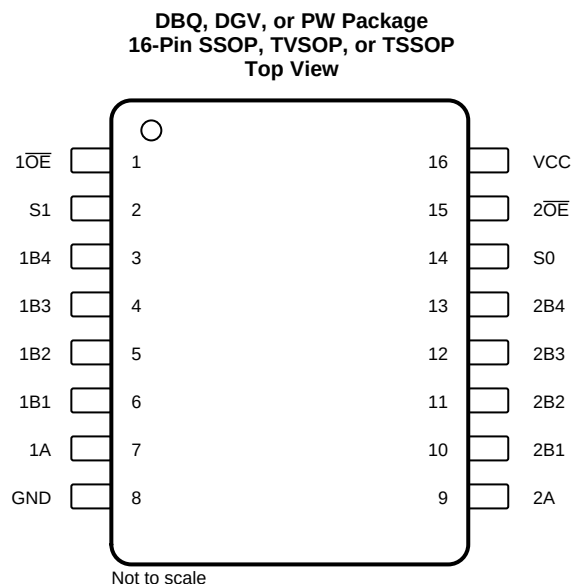
Changes from Revision B (June 2015) to Revision C Page

• Changed the pinout image appearance	3
• Updated the <i>Thermal Information</i> table	5

Changes from Revision A (November 2003) to Revision B Page

• Removed <i>Ordering Information</i> table.	1
• Added <i>Applications</i> , <i>Device Information</i> table, <i>Pin Configuration and Functions</i> section, <i>Storage Conditions</i> table, <i>ESD Ratings</i> table, <i>Feature Description</i> section, <i>Device Functional Modes</i> , <i>Application and Implementation</i> section, <i>Power Supply Recommendations</i> section, <i>Layout</i> section, <i>Device and Documentation Support</i> section, and <i>Mechanical, Packaging, and Orderable Information</i> section	1

5 Pin Configuration and Functions



Pin Functions

PIN		I/O	DESCRIPTION
NAME	NO.		
1OE	1	I	Output Enable 1 Active-Low
S1	2	I	Select Pin 1
1B4	3	I/O	Channel 1 I/O 4
1B3	4	I/O	Channel 1 I/O 3
1B2	5	I/O	Channel 1 I/O 2
1B1	6	I/O	Channel 1 I/O 1
1A	7	I/O	Channel 1 common
GND	8	—	Ground
2A	9	I/O	Channel 2 common
2B1	10	I/O	Channel 2 I/O 1
2B2	11	I/O	Channel 2 I/O 2
2B3	12	I/O	Channel 2 I/O 3
2B4	13	I/O	Channel 2 I/O 4
S0	14	I	Select Pin 0
2OE	15	I	Output Enable 2 Active-Low
VCC	16	—	Power

6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

			MIN	MAX	UNIT
V _{CC}	Supply voltage		−0.5	4.6	V
V _{IN}	Control input voltage ⁽²⁾⁽³⁾		−0.5	7	V
V _{I/O}	Switch I/O voltage ⁽²⁾⁽³⁾⁽⁴⁾		−0.5	7	V
I _{IK}	Control input clamp current	V _{IN} < 0		−50	mA
I _{I/OK}	I/O port clamp current	V _{I/O} < 0		−50	mA
I _{I/O}	ON-state switch current ⁽⁵⁾			±64	mA
	Continuous current through V _{CC} or GND			±100	mA
T _{stg}	Storage temperature		−65	150	°C

- (1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) All voltages are with respect to ground, unless otherwise specified.
- (3) The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
- (4) V_I and V_O are used to denote specific conditions for V_{I/O}.
- (5) I_I and I_O are used to denote specific conditions for I_{I/O}.

6.2 ESD Ratings

		VALUE	UNIT
V _(ESD)	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	+2000
		Charged-device model (CDM), per JEDEC specification JESD22-C101 ⁽²⁾	+1000

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
- (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

		MIN	MAX	UNIT
V _{CC}	Supply voltage	2.3	3.6	V
V _{IH}	High-level control input voltage	V _{CC} = 2.3 V to 2.7 V	1.7	5.5
		V _{CC} = 2.7 V to 3.6 V	2	5.5
V _{IL}	Low-level control input voltage	V _{CC} = 2.3 V to 2.7 V	0	0.7
		V _{CC} = 2.7 V to 3.6 V	0	0.8
V _{I/O}	Data input/output voltage	0	5.5	V
T _A	Operating free-air temperature	−40	85	°C

- (1) All unused control inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, (SCBA004).

6.4 Thermal Information

THERMAL METRIC ⁽¹⁾		SN74CB3Q3253				UNIT
		DBQ (SSOP)	DGV (TVSOP)	PW (TSSOP)	RGY (VQFN)	
		16 PINS	16 PINS	16 PINS	16 PINS	
R _{θJA}	Junction-to-ambient thermal resistance	114.3	126	112.7	45.7	°C/W
R _{θJC(top)}	Junction-to-case (top) thermal resistance	65.4	51.3	47.5	59.6	°C/W
R _{θJB}	Junction-to-board thermal resistance	56.8	57.8	57.85	23.3	°C/W
ψ _{JT}	Junction-to-top characterization parameter	18.3	5.9	6	2.2	°C/W
ψ _{JB}	Junction-to-board characterization parameter	56.4	57.3	57.3	23.4	°C/W
R _{θJC(bot)}	Junction-to-case (bottom) thermal resistance	n/a	n/a	n/a	11.5	°C/W

- (1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC Package Thermal Metrics](#) application report.

6.5 Electrical Characteristics

over recommended operating free-air temperature range (unless otherwise noted)⁽¹⁾

PARAMETER		TEST CONDITIONS		MIN	TYP ⁽²⁾	MAX	UNIT
V _{IK}		V _{CC} = 3.6 V,	I _I = –18 mA			–1.8	V
I _{IN}	Control inputs	V _{CC} = 3.6 V,	V _{IN} = 0 to 5.5 V			±1	μA
I _{OZ} ⁽³⁾		V _{CC} = 3.6 V,	V _O = 0 to 5.5 V, V _I = 0, Switch OFF, V _{IN} = V _{CC} or GND			±1	μA
I _{off}		V _{CC} = 0,	V _O = 0 to 5.5 V, V _I = 0			1	μA
I _{CC}		V _{CC} = 3.6 V,	I _{I/O} = 0, Switch ON or OFF, V _{IN} = V _{CC} or GND		0.6	2	mA
ΔI _{CC} ⁽⁴⁾	Control inputs	V _{CC} = 3.6 V,	One input at 3 V, Other inputs at V _{CC} or GND			30	μA
I _{CCD} ⁽⁵⁾	Per control input	V _{CC} = 3.6 V, Control input switching at 50% duty cycle	A and B ports open, OE input S input		0.15 0.04	0.16 0.05	mA/ MHz
C _{in}	Control inputs	V _{CC} = 3.3 V,	V _{IN} = 5.5 V, 3.3 V, or 0		2.5	3.5	pF
C _{io(OFF)}	A port	V _{CC} = 3.3 V,	Switch OFF, V _{IN} = V _{CC} or GND, V _{I/O} = 5.5 V, 3.3 V, or 0		8	11	pF
	B port	V _{CC} = 3.3 V,	Switch OFF, V _{IN} = V _{CC} or GND, V _{I/O} = 5.5 V, 3.3 V, or 0		3.5	4.5	pF
C _{io(ON)}		V _{CC} = 3.3 V,	Switch ON, V _{IN} = V _{CC} or GND, V _{I/O} = 5.5 V, 3.3 V, or 0		13	17	pF
r _{on} ⁽⁶⁾		V _{CC} = 2.3 V, TYP at V _{CC} = 2.5 V	V _I = 0, I _O = 30 mA		4	10	Ω
			V _I = 1.7 V, I _O = –15 mA		4.5	11	
		V _{CC} = 3 V	V _I = 0, I _O = 30 mA		3.5	8	
			V _I = 2.4 V, I _O = –15 mA		4	10	

- (1) V_{IN} and I_{IN} refer to control inputs. V_I, V_O, I_I, and I_O refer to data pins.
(2) All typical values are at V_{CC} = 3.3 V (unless otherwise noted), T_A = 25°C.
(3) For I/O ports, the parameter I_{OZ} includes the input leakage current.
(4) This is the increase in supply current for each input that is at the specified TTL voltage level, rather than V_{CC} or GND.
(5) This parameter specifies the dynamic power-supply current associated with the operating frequency of a single control input (see [Figure 2](#)).
(6) Measured by the voltage drop between the A and B terminals at the indicated current through the switch. ON-state resistance is determined by the lower of the voltages of the two (A or B) terminals.

6.6 Switching Characteristics

over recommended operating free-air temperature range (unless otherwise noted) (see [Figure 3](#))

PARAMETER	FROM (INPUT)	TO (OUTPUT)	$V_{CC} = 2.5 \text{ V} \pm 0.2 \text{ V}$		$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$		UNIT
			MIN	MAX	MIN	MAX	
$f_{\overline{OE}}$ or $f_S^{(1)}$	$\overline{OE}$ or S	A or B		10		20	MHz
$t_{pd}^{(2)}$	A or B	B or A		0.12		0.18	ns
$t_{pd(s)}$	S	A	1.5	6.7	1.5	5.9	ns
t_{en}	S	B	1.5	6.7	1.5	5.9	ns
	$\overline{OE}$	A or B	1.5	6.7	1.5	5.9	
t_{dis}	S	B	1	6.1	1	6.1	ns
	$\overline{OE}$	A or B	1	6.1	1	6.1	

(1) Maximum switching frequency for control input ($V_O > V_{CC}$, $V_I = 5 \text{ V}$, $R_L \geq 1 \text{ M}\Omega$, $C_L = 0$).

(2) The propagation delay is the calculated RC time constant of the typical ON-state resistance of the switch and the specified load capacitance, when driven by an ideal voltage source (zero output impedance).

6.7 Typical Characteristics

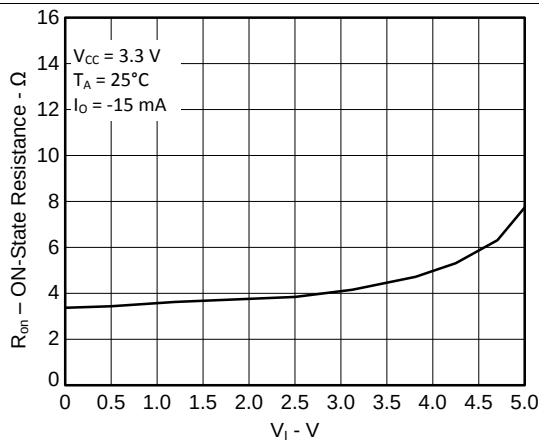


Figure 1. Typical r_{on} vs V_I , $V_{CC} = 3.3 \text{ V}$ and $I_O = -15 \text{ mA}$

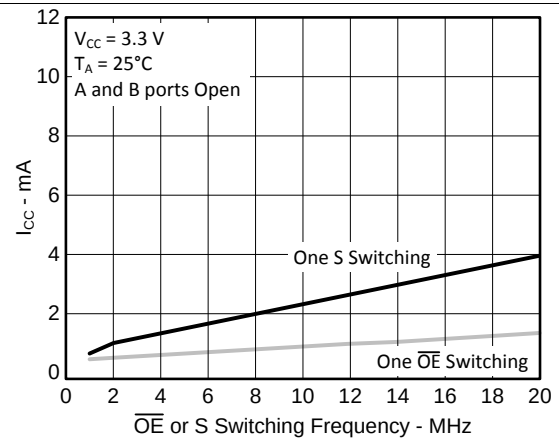
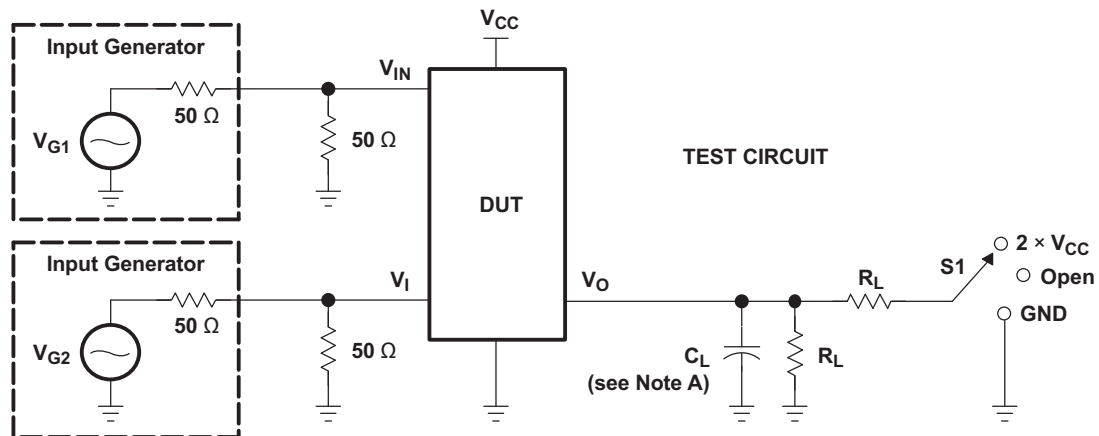
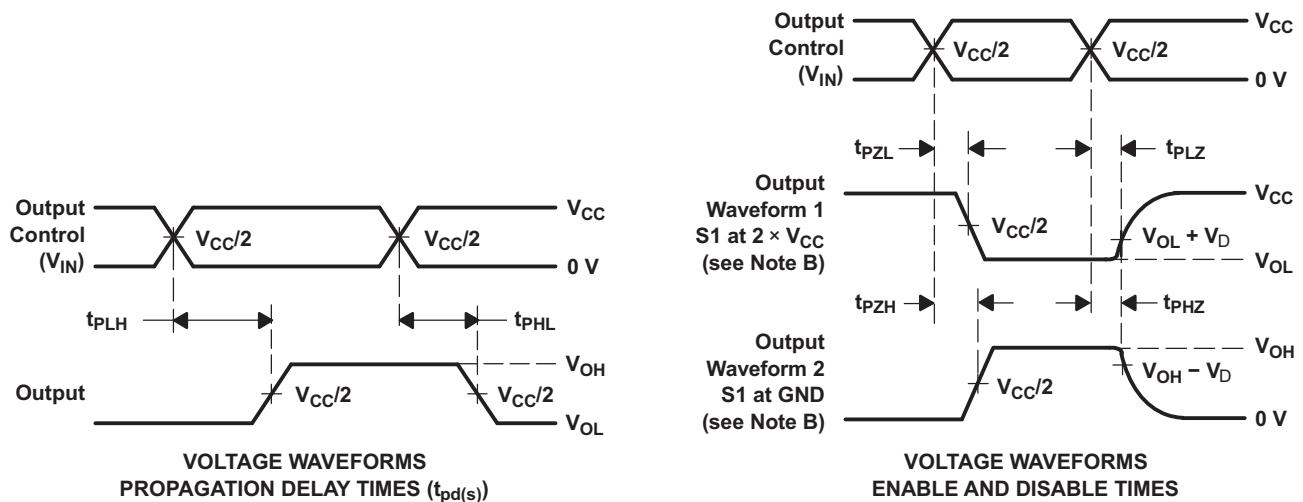


Figure 2. Typical I_{CC} vs $\overline{OE}$ or S Switching Frequency, $V_{CC} = 3.3 \text{ V}$

7 Parameter Measurement Information



TEST	V _{CC}	S1	R _L	V _I	C _L	V _A
t _{pd(s)}	2.5 V ± 0.2 V	Open	500 Ω	V _{CC} or GND	30 pF	
	3.3 V ± 0.3 V	Open	500 Ω	V _{CC} or GND	50 pF	
t _{PLZ} /t _{PZL}	2.5 V ± 0.2 V	2 × V _{CC}	500 Ω	GND	30 pF	0.15 V
	3.3 V ± 0.3 V	2 × V _{CC}	500 Ω	GND	50 pF	0.3 V
t _{PHZ} /t _{PZH}	2.5 V ± 0.2 V	GND	500 Ω	V _{CC}	30 pF	0.15 V
	3.3 V ± 0.3 V	GND	500 Ω	V _{CC}	50 pF	0.3 V



- NOTES:
- C_L includes probe and jig capacitance.
 - Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
 - All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
 - The outputs are measured one at a time, with one transition per measurement.
 - t_{PLZ} and t_{PHZ} are the same as t_{dis}.
 - t_{PZL} and t_{PZH} are the same as t_{en}.
 - t_{PLH} and t_{PHL} are the same as t_{pd(s)}. The t_{pd} propagation delay is the calculated RC time constant of the typical ON-state resistance of the switch and the specified load capacitance, when driven by an ideal voltage source (zero output impedance).
 - All parameters and waveforms are not applicable to all devices.

Figure 3. Test Circuit and Voltage Waveforms

8 Detailed Description

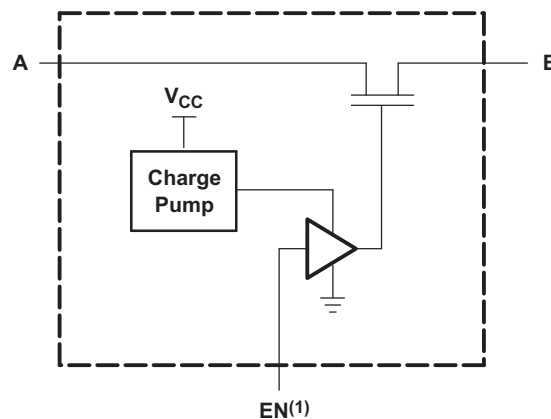
8.1 Overview

The SN74CB3Q3253 device is a high-bandwidth FET bus switch using a charge pump to elevate the gate voltage of the pass transistor, providing a low and flat ON-state resistance (r_{on}). The low and flat ON-state resistance allows for minimal propagation delay and supports rail-to-rail switching on the data input/output (I/O) ports. The device also features low data I/O capacitance to minimize capacitive loading and signal distortion on the data bus. Specifically designed to support high-bandwidth applications, the SN74CB3Q3253 device provides an optimized interface solution ideally suited for broadband communications, networking, and data-intensive computing systems.

The SN74CB3Q3253 device is organized as two 1-of-4 multiplexers/demultiplexers with separate output-enable ($\overline{1OE}$, $2\overline{OE}$) inputs. The select (S0, S1) inputs control the data path of each multiplexer/demultiplexer. When $\overline{OE}$ is low, the associated multiplexer/demultiplexer is enabled, and the A port is connected to the B port, allowing bidirectional data flow between ports. When $\overline{OE}$ is high, the associated multiplexer/demultiplexer is disabled, and a high-impedance state exists between the A and B ports.

This device is fully specified for partial-power-down applications using I_{off} . The I_{off} circuitry prevents damaging current backflow through the device when it is powered down. The device has isolation during power off.

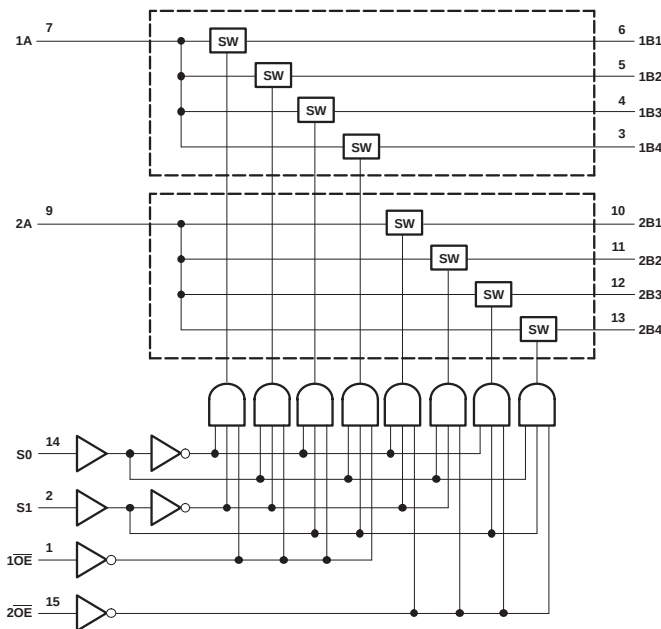
To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.



(1) EN is the internal enable signal applied to the switch.

Figure 4. Simplified Schematic, Each FET Switch (SW)

8.2 Functional Block Diagram



8.3 Feature Description

The SN74CB3Q3253 device has a high-bandwidth data path (up to 500 MHz) and has 5-V tolerant I/Os with the device powered up or powered down. It also has low and flat ON-state resistance (r_{on}) characteristics over operating range ($r_{on} = 4 \Omega$ Typical)

This device also has rail-to-rail switching on data I/O ports for 0- to 5-V switching with 3.3-V V_{CC} and 0- to 3.3-V switching with 2.5-V V_{CC} as well as bidirectional data flow with near-zero propagation delay and low input and output capacitance that minimizes loading and signal distortion ($C_{io(OFF)} = 3.5$ pF Typical)

The SN74CB3Q3253 also provides a fast switching frequency ($f_{OE} = 20$ MHz Maximum) with data and control inputs that provide undershoot clamp diodes as well as low power consumption ($I_{CC} = 0.6$ mA Typical)

The V_{CC} operating range is from 2.3 V to 3.6 V and the data I/Os support 0- to 5-V signal levels of (0.8-V, 1.2-V, 1.5-V, 1.8-V, 2.5-V, 3.3-V, 5-V)

The control inputs can be driven by TTL or 5-V and 3.3-V CMOS outputs as well as I_{off} Supports Partial-Power-Down Mode Operation

8.4 Device Functional Modes

Table 1 lists the functional modes of the SN74CB3Q3253.

**Table 1. Function Table
(Each Multiplexer/Demultiplexer)**

INPUTS			INPUT/OUTPUT	FUNCTION
$\overline{OE}$	S1	S0	A	
L	L	L	B1	A port = B1 port
L	L	H	B2	A port = B2 port
L	H	L	B3	A port = B3 port
L	H	H	B4	A port = B4 port
H	X	X	Z	Disconnect

9 Application and Implementation

NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

9.1 Application Information

The SN74CB3Q3253 device can be used to multiplex and demultiplex up to 4 channels simultaneously in a 2:1 configuration.

9.2 Typical Application

The application shown here is a 4-bit bus being multiplexed between two devices. the $\overline{OE}$ and S pins are used to control the chip from the bus controller. This is a very generic example, and could apply to many situations. If an application requires less than 4 bits, be sure to tie the A side to either high or low on unused channels.

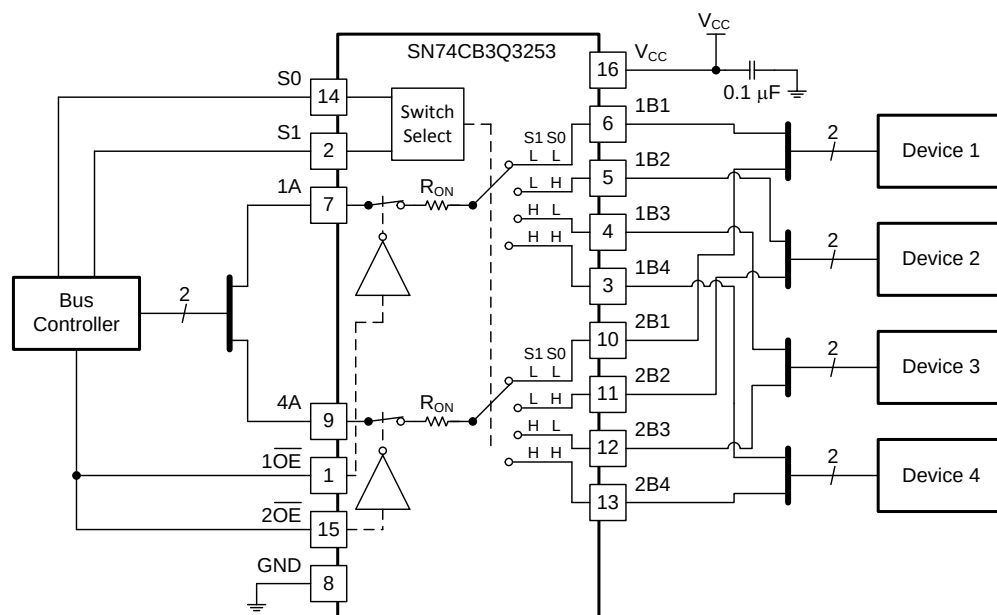


Figure 5. Typical Application of the SN74CB3Q3253

9.2.1 Design Requirements

The 0.1-μF capacitor should be placed as close as possible to the device.

9.2.2 Detailed Design Procedure

- Recommended Input Conditions:
 - For specified high and low levels, see V_{IH} and V_{IL} in [Recommended Operating Conditions](#).
 - Inputs and outputs are overvoltage tolerant allowing them to go as high as 4.6 V at any valid V_{CC} .
- Recommended Output Conditions:
 - Load currents should not exceed ± 128 mA per channel.
- Frequency Selection Criterion:
 - Maximum frequency tested is 500 MHz.
 - Added trace resistance and capacitance can reduce maximum frequency capability; use layout practices as directed in [Layout](#).

Typical Application (continued)

9.2.3 Application Curve

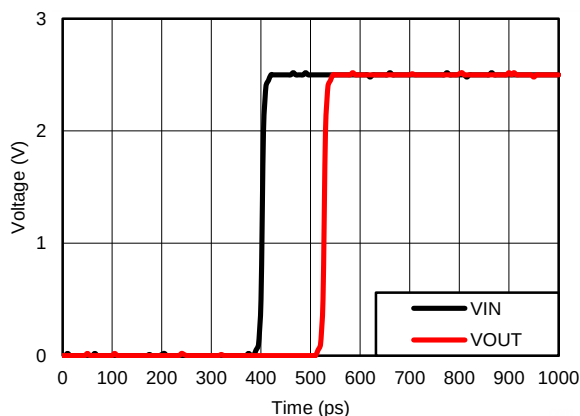


Figure 6. Propagation Delay (t_{pd}) Simulation Result at $V_{CC} = 2.5\text{ V}$

10 Power Supply Recommendations

The power supply can be any voltage between the minimum and maximum supply voltage rating listed in the [Absolute Maximum Ratings](#) table.

Each V_{CC} terminal should have a good bypass capacitor to prevent power disturbance. For devices with a single supply, a 0.1- μF bypass capacitor is recommended. If multiple pins are labeled V_{CC} , then a 0.01- μF or 0.022- μF capacitor is recommended for each V_{CC} because the V_{CC} pins are tied together internally. For devices with dual-supply pins operating at different voltages, for example V_{CC} and V_{DD} , a 0.1- μF bypass capacitor is recommended for each supply pin. To reject different frequencies of noise, use multiple bypass capacitors in parallel. Capacitors with values of 0.1 μF and 1 μF are commonly used in parallel. The bypass capacitor should be installed as close to the power terminal as possible for best results.

11 Layout

11.1 Layout Guidelines

Reflections and matching are closely related to the loop antenna theory but are different enough to be discussed separately from the theory. When a PCB trace turns a corner at a 90° angle, a reflection can occur. A reflection occurs primarily because of the change of width of the trace. At the apex of the turn, the trace width increases to 1.414 times the width. This increase upsets the transmission-line characteristics, especially the distributed capacitance and self-inductance of the trace which results in the reflection. Not all PCB traces can be straight and therefore some traces must turn corners. [Figure 7](#) shows progressively better techniques of rounding corners. Only the last example (BEST) maintains constant trace width and minimizes reflections.

11.2 Layout Example

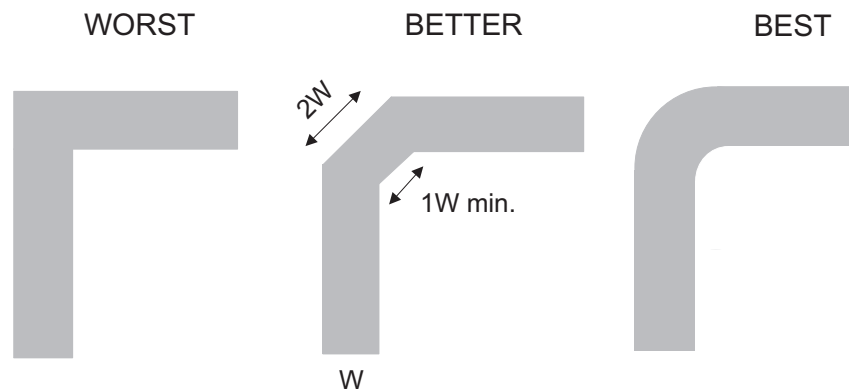


Figure 7. Trace Example

12 Device and Documentation Support

12.1 Documentation Support

12.1.1 Related Documentation

For related documentation see the following:

- *Implications of Slow or Floating CMOS Inputs*, [SCBA004](#)
- *Selecting the Right Texas Instruments Signal Switch*, [SZZA030](#)

12.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. In the upper right corner, click on *Alert me* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

12.3 Community Resources

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's [Terms of Use](#).

TI E2E™ Online Community *TI's Engineer-to-Engineer (E2E) Community*. Created to foster collaboration among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

Design Support *TI's Design Support* Quickly find helpful E2E forums along with design support tools and contact information for technical support.

12.4 Trademarks

E2E is a trademark of Texas Instruments.

All other trademarks are the property of their respective owners.

12.5 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

12.6 Glossary

[SLYZ022](#) — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGING INFORMATION

Orderable part number	Status (1)	Material type (2)	Package Pins	Package qty Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
SN74CB3Q3253DBQR	Active	Production	SSOP (DBQ) 16	2500 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	BU253
SN74CB3Q3253DBQR.A	Active	Production	SSOP (DBQ) 16	2500 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	BU253
SN74CB3Q3253DBQR.B	Active	Production	SSOP (DBQ) 16	2500 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	BU253
SN74CB3Q3253DBQRG4	Active	Production	SSOP (DBQ) 16	2500 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	BU253
SN74CB3Q3253DBQRG4.A	Active	Production	SSOP (DBQ) 16	2500 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	BU253
SN74CB3Q3253DBQRG4.B	Active	Production	SSOP (DBQ) 16	2500 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	BU253
SN74CB3Q3253DGVR	Active	Production	TVSOP (DGV) 16	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	BU253
SN74CB3Q3253DGVR.B	Active	Production	TVSOP (DGV) 16	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	BU253
SN74CB3Q3253DGVRG4	Active	Production	TVSOP (DGV) 16	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	BU253
SN74CB3Q3253DGVRG4.B	Active	Production	TVSOP (DGV) 16	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	BU253
SN74CB3Q3253PW	Obsolete	Production	TSSOP (PW) 16	-	-	Call TI	Call TI	-40 to 85	BU253
SN74CB3Q3253PWR	Active	Production	TSSOP (PW) 16	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	BU253
SN74CB3Q3253PWR.A	Active	Production	TSSOP (PW) 16	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	BU253
SN74CB3Q3253PWR.B	Active	Production	TSSOP (PW) 16	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	BU253
SN74CB3Q3253RGYR	Active	Production	VQFN (RGY) 16	3000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	BU253
SN74CB3Q3253RGYR.A	Active	Production	VQFN (RGY) 16	3000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	BU253
SN74CB3Q3253RGYR.B	Active	Production	VQFN (RGY) 16	3000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	BU253
SN74CB3Q3253RGYRG4	Active	Production	VQFN (RGY) 16	3000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	BU253
SN74CB3Q3253RGYRG4.A	Active	Production	VQFN (RGY) 16	3000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	BU253
SN74CB3Q3253RGYRG4.B	Active	Production	VQFN (RGY) 16	3000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	BU253

⁽¹⁾ **Status:** For more details on status, see our [product life cycle](#).

⁽²⁾ **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

⁽³⁾ **RoHS values:** Yes, No, RoHS Exempt. See the [TI RoHS Statement](#) for additional information and value definition.

(4) **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

(5) **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

(6) **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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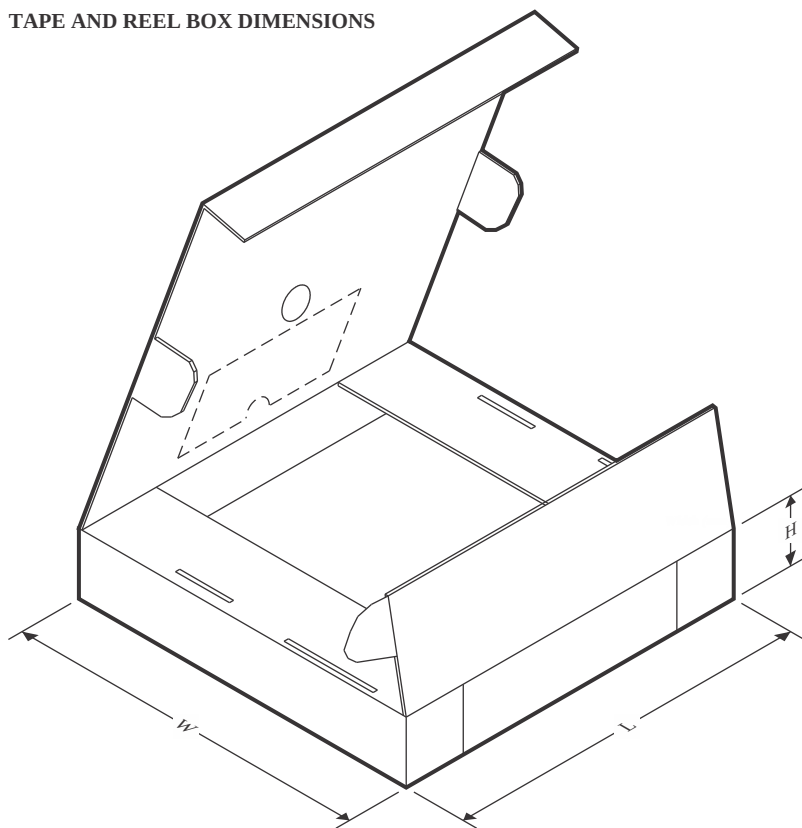
TAPE AND REEL INFORMATION



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74CB3Q3253DBQR	SSOP	DBQ	16	2500	330.0	12.5	6.4	5.2	2.1	8.0	12.0	Q1
SN74CB3Q3253DBQRG4	SSOP	DBQ	16	2500	330.0	12.5	6.4	5.2	2.1	8.0	12.0	Q1
SN74CB3Q3253DGVR	TVSOP	DGV	16	2000	330.0	12.4	6.8	4.0	1.6	8.0	12.0	Q1
SN74CB3Q3253DGVRG4	TVSOP	DGV	16	2000	330.0	12.4	6.8	4.0	1.6	8.0	12.0	Q1
SN74CB3Q3253PWR	TSSOP	PW	16	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
SN74CB3Q3253RGYR	VQFN	RGY	16	3000	330.0	12.4	3.8	4.3	1.5	8.0	12.0	Q1
SN74CB3Q3253RGYRG4	VQFN	RGY	16	3000	330.0	12.4	3.8	4.3	1.5	8.0	12.0	Q1

TAPE AND REEL BOX DIMENSIONS



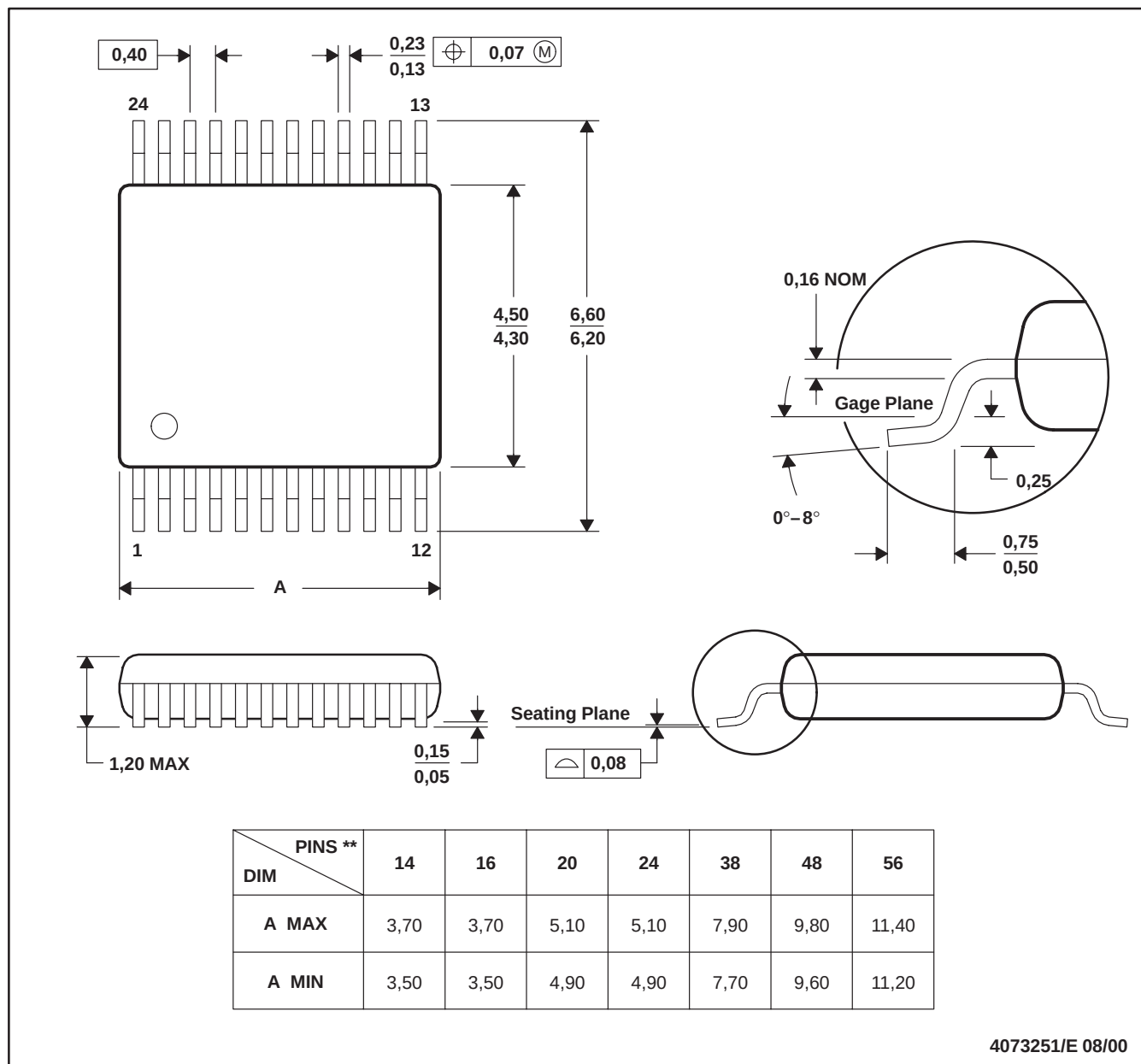
*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74CB3Q3253DBQR	SSOP	DBQ	16	2500	353.0	353.0	32.0
SN74CB3Q3253DBQRG4	SSOP	DBQ	16	2500	353.0	353.0	32.0
SN74CB3Q3253DGVR	TVSOP	DGV	16	2000	353.0	353.0	32.0
SN74CB3Q3253DGVRG4	TVSOP	DGV	16	2000	353.0	353.0	32.0
SN74CB3Q3253PWR	TSSOP	PW	16	2000	353.0	353.0	32.0
SN74CB3Q3253RGYR	VQFN	RGY	16	3000	353.0	353.0	32.0
SN74CB3Q3253RGYRG4	VQFN	RGY	16	3000	353.0	353.0	32.0

DGV (R-PDSO-G**)

PLASTIC SMALL-OUTLINE

24 PINS SHOWN



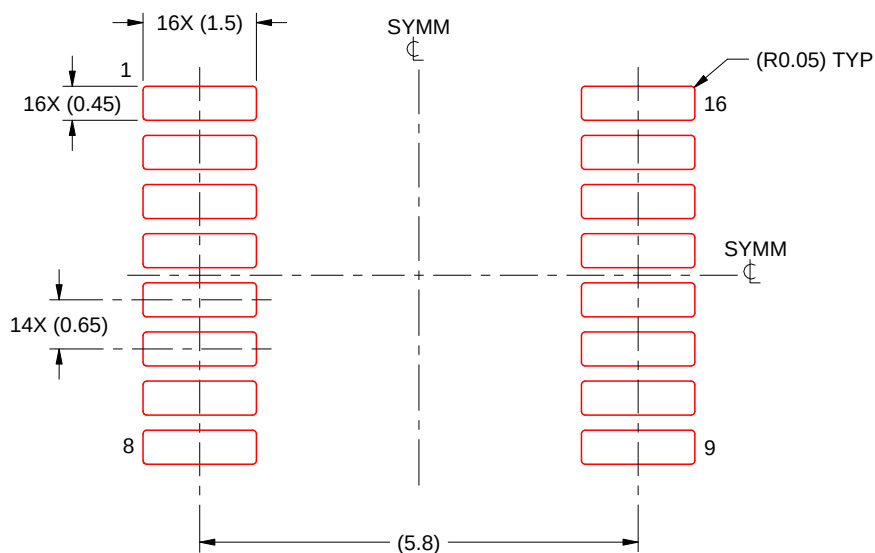
- NOTES: A. All linear dimensions are in millimeters.
 B. This drawing is subject to change without notice.
 C. Body dimensions do not include mold flash or protrusion, not to exceed 0,15 per side.
 D. Falls within JEDEC: 24/48 Pins – MO-153
 14/16/20/56 Pins – MO-194

EXAMPLE STENCIL DESIGN

PW0016A

TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE

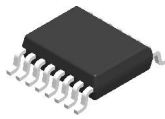


SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE: 10X

4220204/B 12/2023

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

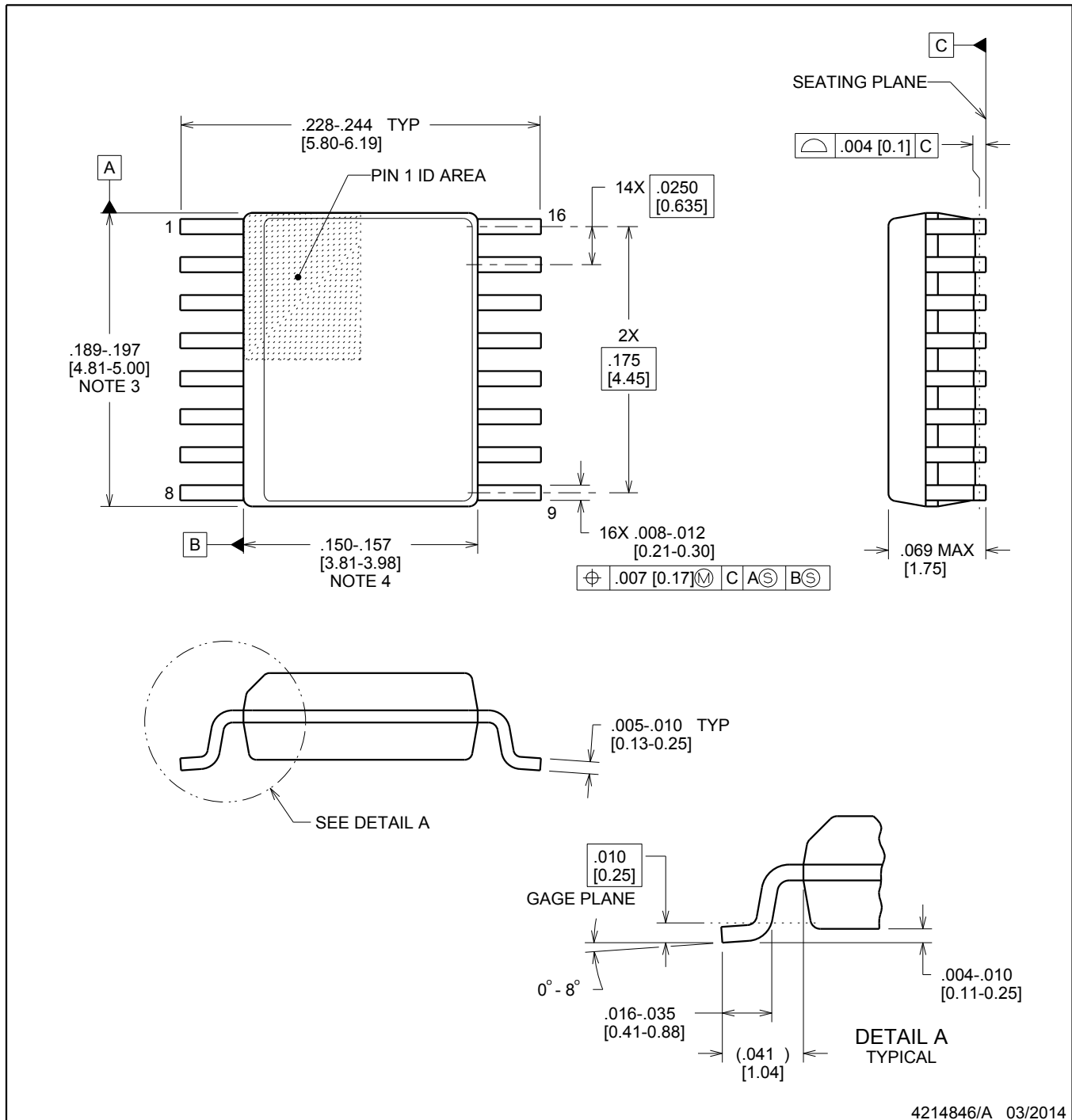


DBQ0016A

PACKAGE OUTLINE

SSOP - 1.75 mm max height

SHRINK SMALL-OUTLINE PACKAGE



4214846/A 03/2014

NOTES:

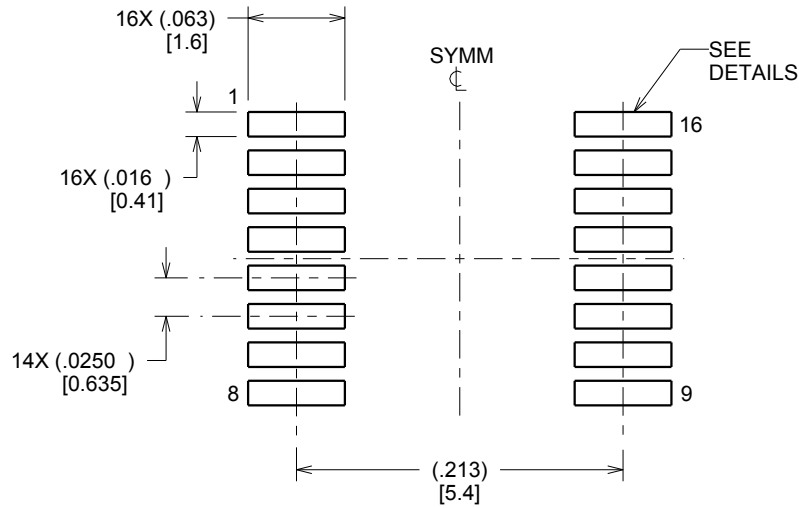
- Linear dimensions are in inches [millimeters]. Dimensions in parenthesis are for reference only. Controlling dimensions are in inches. Dimensioning and tolerancing per ASME Y14.5M.
- This drawing is subject to change without notice.
- This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed .006 inch, per side.
- This dimension does not include interlead flash.
- Reference JEDEC registration MO-137, variation AB.

EXAMPLE BOARD LAYOUT

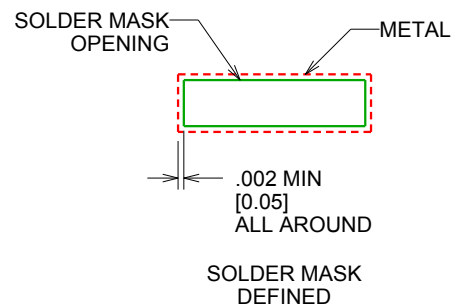
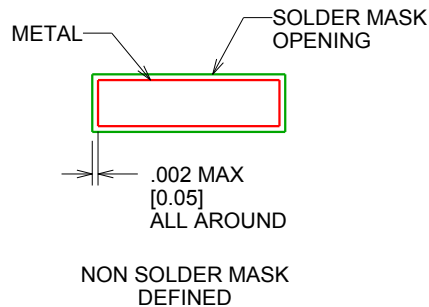
DBQ0016A

SSOP - 1.75 mm max height

SHRINK SMALL-OUTLINE PACKAGE



LAND PATTERN EXAMPLE
SCALE:8X



SOLDER MASK DETAILS

4214846/A 03/2014

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

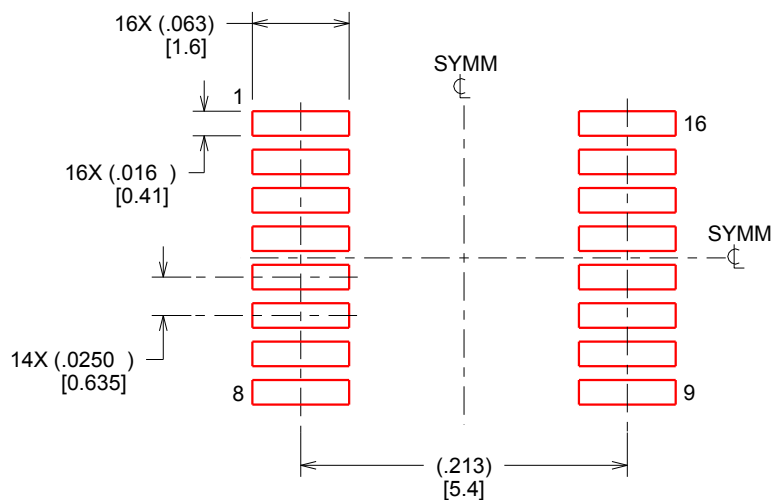
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

DBQ0016A

SSOP - 1.75 mm max height

SHRINK SMALL-OUTLINE PACKAGE



SOLDER PASTE EXAMPLE
BASED ON .005 INCH [0.127 MM] THICK STENCIL
SCALE:8X

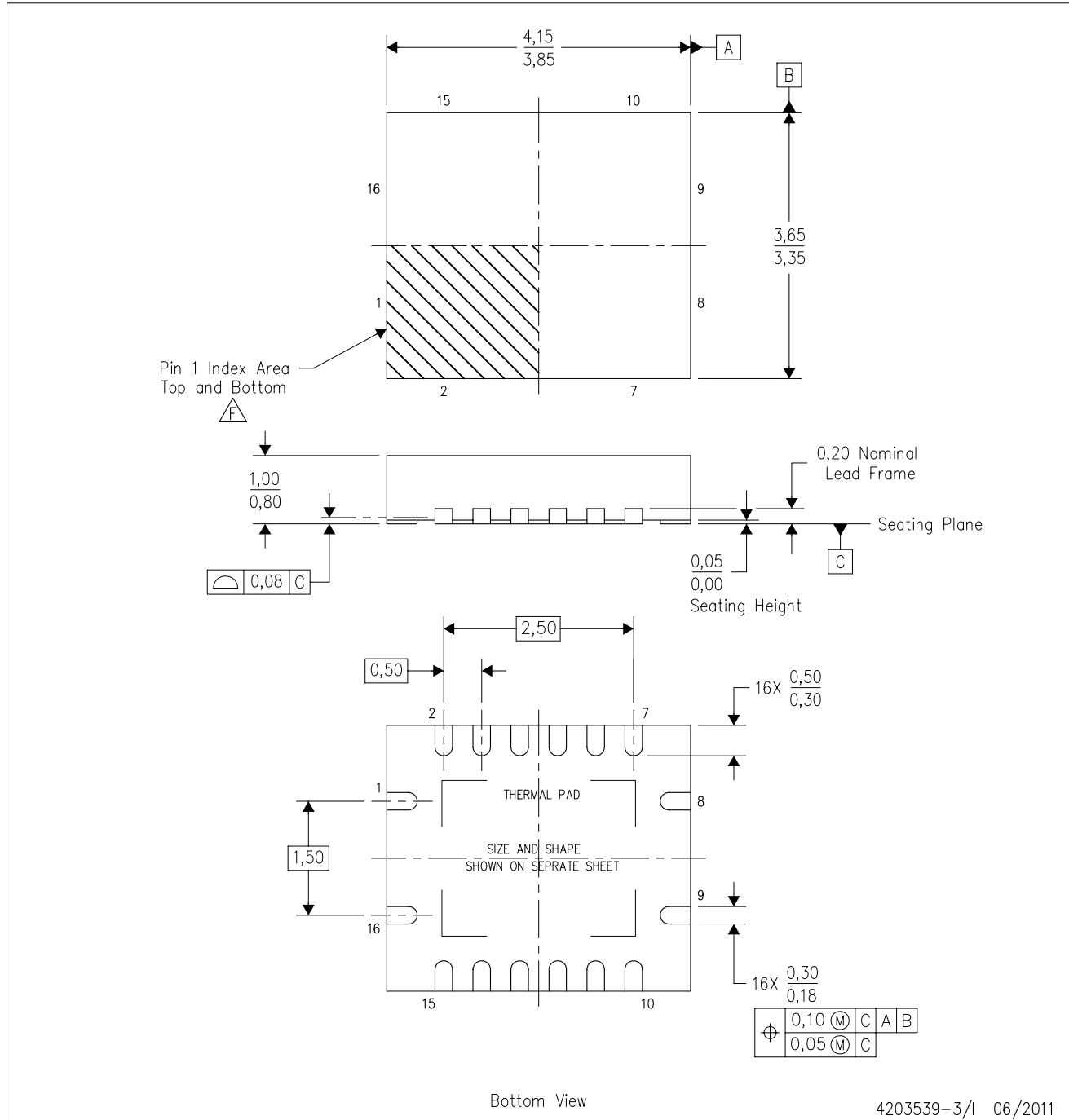
4214846/A 03/2014

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

RGY (R-PVQFN-N16)

PLASTIC QUAD FLATPACK NO-LEAD



4203539-3/I 06/2011

- NOTES:
- All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994.
 - This drawing is subject to change without notice.
 - QFN (Quad Flatpack No-Lead) package configuration.
 - The package thermal pad must be soldered to the board for thermal and mechanical performance.
 - See the additional figure in the Product Data Sheet for details regarding the exposed thermal pad features and dimensions.
- F** Pin 1 identifiers are located on both top and bottom of the package and within the zone indicated. The Pin 1 identifiers are either a molded, marked, or metal feature.
- Package complies to JEDEC MO-241 variation BA.

RGY (R-PVQFN-N16)

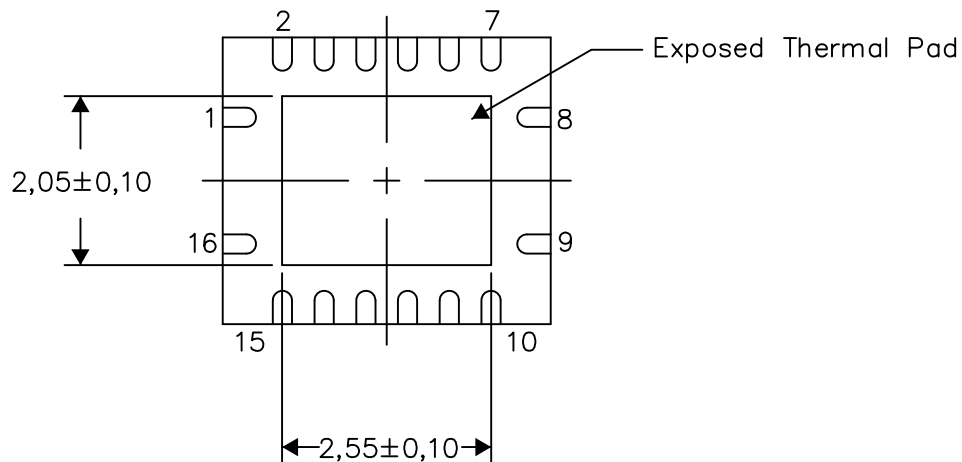
PLASTIC QUAD FLATPACK NO-LEAD

THERMAL INFORMATION

This package incorporates an exposed thermal pad that is designed to be attached directly to an external heatsink. The thermal pad must be soldered directly to the printed circuit board (PCB). After soldering, the PCB can be used as a heatsink. In addition, through the use of thermal vias, the thermal pad can be attached directly to the appropriate copper plane shown in the electrical schematic for the device, or alternatively, can be attached to a special heatsink structure designed into the PCB. This design optimizes the heat transfer from the integrated circuit (IC).

For information on the Quad Flatpack No-Lead (QFN) package and its advantages, refer to Application Report, QFN/SON PCB Attachment, Texas Instruments Literature No. SLUA271. This document is available at www.ti.com.

The exposed thermal pad dimensions for this package are shown in the following illustration.

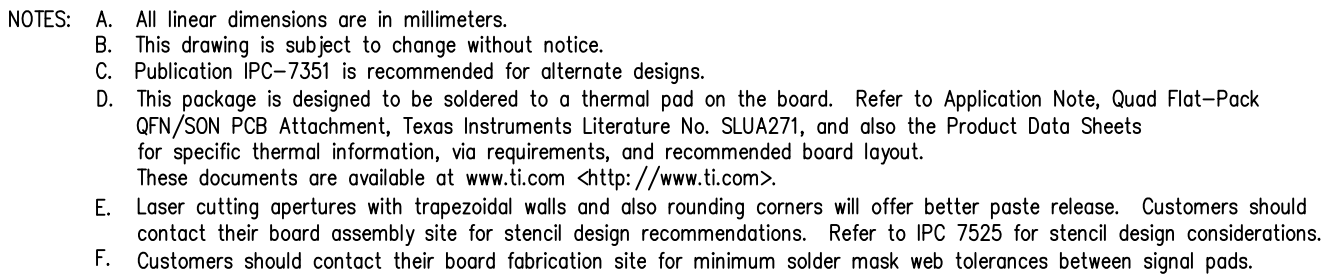


Bottom View

Exposed Thermal Pad Dimensions

4206353-3/P 03/14

NOTE: All linear dimensions are in millimeters



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